

AF/GAU 2822



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes
Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

Docket No.: 303.229US2
Filed: August 11, 1998
Examiner: Mark V. Prenty

Serial No.: 09/132,157
Due Date: January 30, 2001
Group Art Unit: 2822

Box AF
Commissioner for Patents
Washington, D.C. 20231

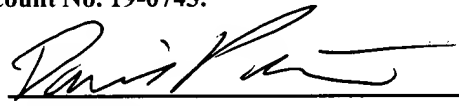
We are transmitting herewith the following attached items (as indicated with an "X"):

- X A return postcard.
- X An Amendment and Response After Final (7 Pages).

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Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

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By: 
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Box AF, Commissioner for Patents, Washington, D.C. 20231, on this 22 day of December, 2000.

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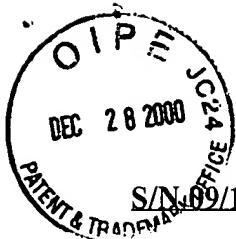
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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
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EXPEDITED PROCEDURE - EXAMINING GROUP 2822

S/N 09/132,157

PATENT

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AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116

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In response to the Final Office Action mailed October 30, 2000, please amend the application as follows.

IN THE CLAIMS

Please cancel claims 30-31 without prejudice or disclaimer. Please amend claims 11, 24, 25, 28, 32, 38-41, and 43 as follows. Claims 11, 13-14, 24-28, 32, 38-43 are now pending in the application.

11. (Five times amended) A p-channel metal-oxide-semiconductor transistor, comprising:
- a silicon substrate;
 - a silicon dioxide (SiO_2) gate oxide, coupled to the substrate;
 - a gate, coupled to the SiO_2 gate oxide;
 - source/drain regions formed in the substrate on opposite sides of the gate; and
 - a $\text{Si}_{1-x}\text{Ge}_x$ channel region, having a germanium molar fraction x , located underneath [and formed in the substrate, underneath and adjoining] the SiO_2 gate oxide and between the source/drain regions[;], wherein x is less than or equal to 0.6, and wherein the $\text{Si}_{1-x}\text{Ge}_x$ channel region forms a $\text{Si}_{1-x}\text{Ge}_x/\text{SiO}_2$ gate oxide interface.
- [wherein the $\text{Si}_{1-x}\text{Ge}_x$ channel region has a channel length less than $7\mu\text{m}$.]

24. (Five times amended) A p-channel metal-oxide-semiconductor transistor formed on a silicon substrate, comprising: